

a step (b-5) of forming insulation layers between the first signal electrodes after the step (b-1),

wherein upper surfaces of the insulation layers are on the same level as upper surfaces of the first signal electrodes.

49. (Amended) An embedded device comprising:  
the ferroelectric memory device as defined in claim 1; and  
at least one component selected from a group including a flash memory, a processor, an analog circuit, and an SRAM.

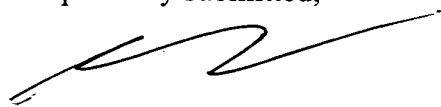
REMARKS

Claims 1-49 are pending. By this Preliminary Amendment, the specification and claims 35-37, 47 and 49 are amended. No new matter is added.

The attached Appendix includes marked-up copies of each rewritten paragraph (37 C.F.R. §1.121(b)(1)(iii)) and claim (37 C.F.R. §1.121(c)(1)(ii)).

Prompt and favorable examination on the merits is respectfully requested.

Respectfully submitted,

  
James A. Oliff  
Registration No. 27,075

Eric D. Morehouse  
Registration No. 38,565

JAO:EDM/gam

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**OLIFF & BERRIDGE, PLC**  
**P.O. Box 19928**  
**Alexandria, Virginia 22320**  
**Telephone: (703) 836-6400**

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